

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
60V	3Ω @ V _{GS} = 10V	SOT23	310mA
607	4Ω @ V _{GS} = 5V	30123	270mA

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

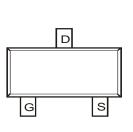
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating Matte Tin Finish Annealed over Alloy 42 Leadframe). (€3)
- Weight: 0.006 grams (Approximate)

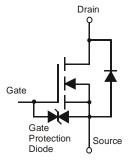




Top View







Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN65D8LQ-7	SOT23	3,000/Tape & Reel
DMN65D8LQ-13	SOT23	10,000/Tape & Reel

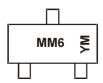
SOT23

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



MM6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	2011		2015	2010	6 20°	17 20	018 2	2019	2020	2021	2022	2023
Code	Υ		С	D	Е		F	G	Н	ı	J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	310 240	mA
Continuous Drain Current (Note 7) V _{GS} = 5V	I _D	270 210	mA		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	800	mA		
Maximum Body Diode Continuous Current (Note 6)			Is	500	mA

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Dawer Dissination	(Note 7)	0	370	mW	
Total Power Dissipation	(Note 6)	P_{D}	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 7)	D	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	R ₀ JC	91			
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

^{7.} Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.2	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	2	3	Ω	$V_{GS} = 10V, I_D = 0.115A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2.5	4	Ω	$V_{GS} = 5V, I_D = 0.115A$
Forward Transconductance	g FS	80	290		mS	$V_{DS} = 10V, I_D = 0.115A$
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	22.0	_		
Output Capacitance	Coss	_	3.2		pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	2.0	_		
Gate Resistance	R_{G}	_	79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V _{GS} = 10V	Qg	_	0.87	_		
Total Gate Charge V _{GS} = 4.5V	Q_{g}	_	0.43	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	Qgs	_	0.11	—	nc nc	$I_D = 150 \text{mA}$
Gate-Drain Charge	Q _{gd}	_	0.11	_		
Turn-On Delay Time	t _{D(on)}	_	2.7	—		
Turn-On Rise Time	t _r	_	2.8	_	nS	$V_{DD} = 30V$, $I_D = 0.115A$, $V_{GEN} = 10V$.
Turn-Off Delay Time	t _{D(off)}	_	12.6	_	110	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t _f	_	7.3	_		

Notes:

^{8.} Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.



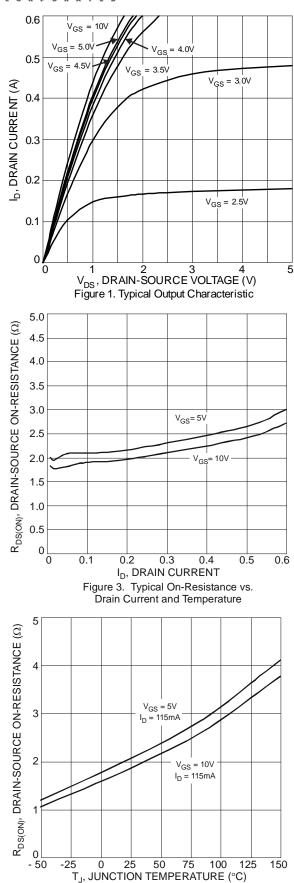
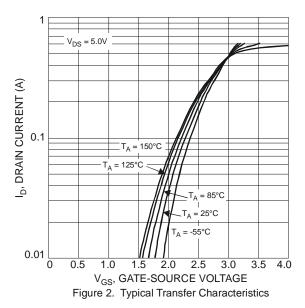
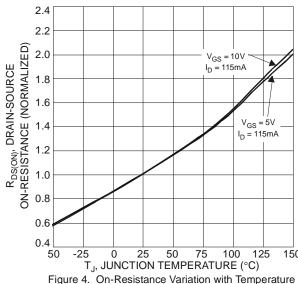


Figure 5. On-Resistance Variation with Temperature

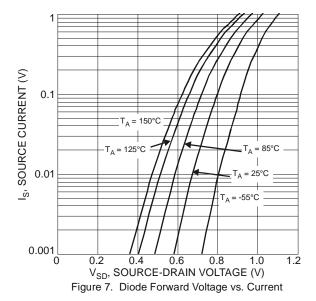




2.0 1.8 V_{GS(th)}, GATE THRESHOLD VOLTAGE (V) 1.6 1.4 1.2 = 250µA 1.0 0.8 0.6 0.4 0.2 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. Gate Threshold Variation vs. Ambient Temperature





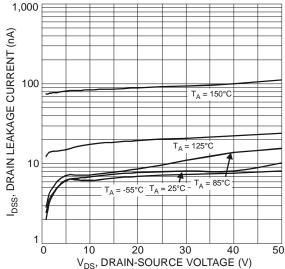
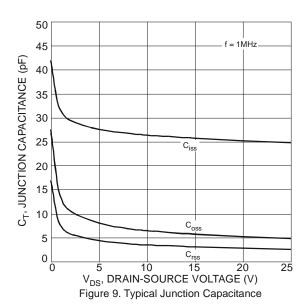
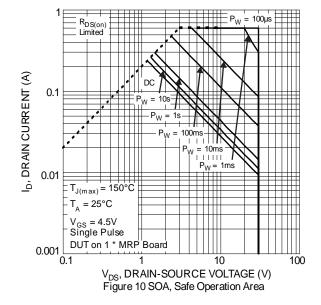
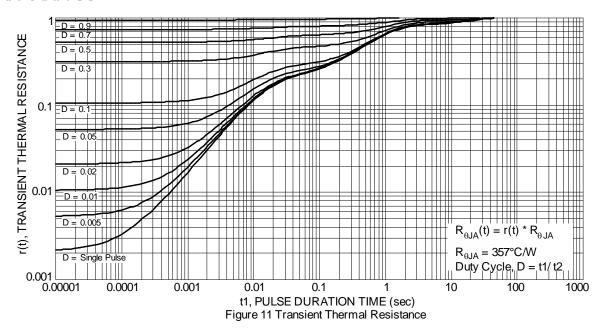


Figure 8. Typical Drain-Source Leakage Current vs. Voltage







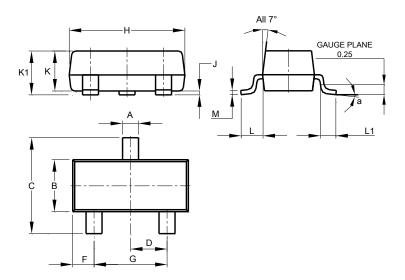




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT23

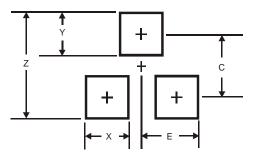


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а		8°					
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.





Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com

DMN65D8LQ Document number: DS38179 Rev. 1 - 2

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))